

<b>INFORMATION DISCLOSURE CITATION</b> MPEP-1449	<b>CUSTOMER NUMBER</b>  26615		ATTORNEY'S DKT No. H1130		APPLICATION No. 10/614,177	
			APPLICANT(s) Bin YU et al.			
			FILING DATE July 8, 2003		GROUP 2811	

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
RR	2002/0137271	9-26-02	Forbes et al.			
	5,411,905	5-2-95	Acovic et al.			
	2003/0178670	9-25-03	Fried et al.			
RR	2002/0072170	6-13-02	Lam			

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No


  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	

EXAMINER <i>H. Rose</i>	DATE CONSIDERED 11/9/04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		 <b>26615</b> <small>PATENT TRADEMARK OFFICE</small>		ATTORNEY'S DKT No. H1130		APPLICATION No. Unassigned	
				APPLICANT(S) Bin YU et al.			
				FILING DATE July 8, 2003		GROUP Unassigned	

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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

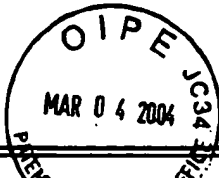
  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
KR	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.
	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.
	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.
	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.
KR	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.

EXAMINER <i>[Signature]</i>	DATE CONSIDERED 11/9/04
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SHEET 1 OF 1

<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449	<b>CUSTOMER NUMBER</b>  26615	ATTORNEY'S DKT No. H1130	APPLICATION No. 10/614,177				
		APPLICANT(S) Bin YU et al.					
		FILING DATE July 8, 2003	GROUP 2811				
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<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
RR	Copy of co-pending U.S. Patent Application No. 10/770,010; by Yider Wu et al., filed February 3, 2004 entitled: "Non-Volatile Memory Device," 21 page specification, 11 sheets of drawings.						
RR	Copy of co-pending U.S. Patent Application No. 10/632,971; by Ming-Ren Lin et al., filed August 4, 2003 entitled: "FinFET Flash Memory," 11 page specification, 9 sheets of drawings.						
EXAMINER <i>K. Rose</i>				DATE CONSIDERED 11/9/04			

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<b>TYPE INFORMATION DISCLOSURE CITATION</b> SEP 15 2004 PTO-1449	<b>CUSTOMER NUMBER</b>  45114	<b>ATTORNEY'S DKT No.</b> H1130	<b>APPLICATION No.</b> 10/614,177
		<b>APPLICANT(S)</b> Bin Yu et al.	
		<b>FILING DATE</b> July 8, 2003	<b>GROUP</b> 2811

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

RR	Copy of co-pending U.S. Patent Application No. 10/929,538 by Yu et al., filed August 31, 2004, entitled "Non-Volatile Memory Device", 25 pages

<b>EXAMINER</b> <i>Kushy Rose</i>	<b>DATE CONSIDERED</b> 11/9/04
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